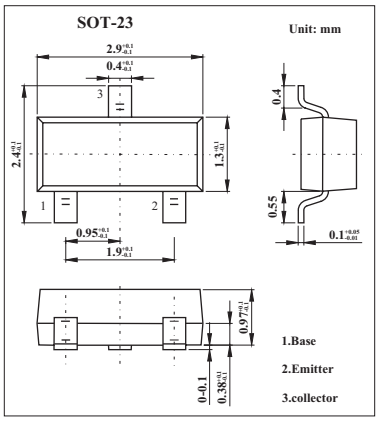
Silicon PNP Epitaxia

2SA1365



■ Features

- Low collector to emitter saturation voltage.
- Excellent linearity nof DC forward current gain.
- Super mini package for easy mounting.
- High collector current.
- High gain band width product.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-25	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-4	V
Peak collector current	I_{CM}	-1	A
Collector current	I_C	-700	mA
Collector dissipation (Ta=25℃)	P_C	150	mW
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = -10 μA, I_E = 0	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = -100 μA,R_{BE} = ∞	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = -10 μA, I_C = 0	-4			V
Collector cut-off current	I_{CBO}	V_{CB} = -25 V, I_E = 0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = -2 V, I_C = 0			-1	μA
DC current gain (*)	h_{FE}	V_{CE} = -4 V, I_C = -100 mA	150		800	
Collector-emitter saturation voltage	V_{CE}	I_C = -500 mA, I_B = -25 mA		-0.2	-0.5	V
Gain band width product	f_T	V_{CE} = -6 V, I_E = 10 mA		180		MHz

* It shows h_{FE} classification in right table.

■ h_{FE} Classification

Marking	AE	AF	AG
hFE	150～300	250～500	400～800